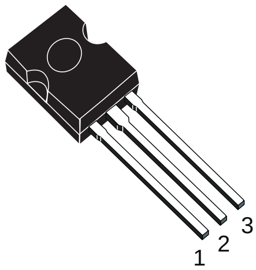
BULK128D-B

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED



SOT-82

APPLICATIONS:
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

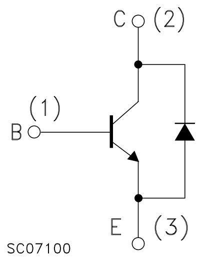
DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is designed for use in lighting applications and low cost switch-mode power supplies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage (V_{BE} = 0)	700	V
V_{CEO}	Collector-Emitter Voltage (I_B = 0)	400	V
V_{EBO}	Emitter-Base Voltage (I_C = 0, I_B = 2 A, t_p < 10μs, T_j < 150°C)	BV_{EBO}	V
I_C	Collector Current	4	A
I_{CM}	Collector Peak Current (t_p < 5 ms)	8	A
I_B	Base Current	2	A
I_{BM}	Base Peak Current (t_p < 5 ms)	4	A
P_{tot}	Total Dissipation at T_c = 25 °C	55	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

THERMAL DATA

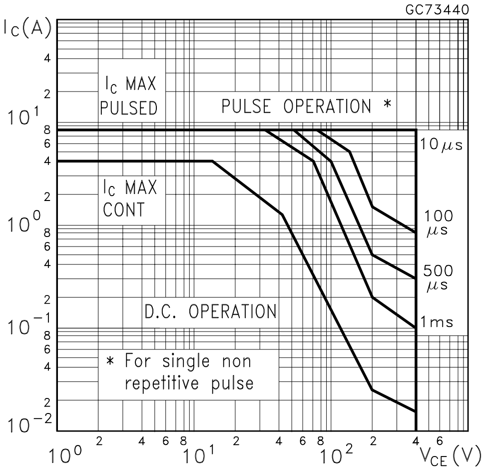
$R_{thj\text{-}case}$	Thermal Resistance Junction-Case Max	2.27	$^oC/W$
$R_{thj\text{-}amb}$	Thermal Resistance Junction-Ambient Max	80	$^oC/W$

ELECTRICAL CHARACTERISTICS (T_{case} = 25 ^oC unless otherwise specified)

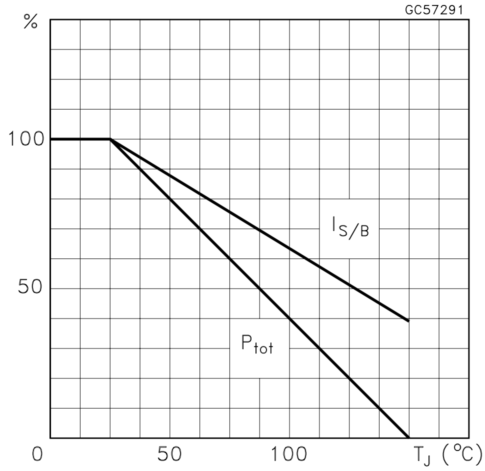
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current (V_{BE} = -1.5 V)	V_{CE} = 700 V V_{CE} = 700 V T_C = 125 ^oC			100 500	μA μA
I_{CEO}	Collector-Emitter Leakage Current (I_B = 0)	V_{CE} = 400 V			250	μA
BV_{EBO}	Emitter-Base Breakdown Voltage (I_C = 0)	I_E = 10 mA	9		18	V
$V_{CEO(sus)}$*	Collector-Emitter Sustaining Voltage (I_B = 0)	I_C = 100 mA L = 25 mH	400			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C = 0.5 A I_B = 0.1 A I_C = 1 A I_B = 0.2 A I_C = 2.5 A I_B = 0.5 A			0.7 1 1.5	V V V
$V_{BE(sat)}$*	Base-Emitter Saturation Voltage	I_C = 0.5 A I_B = 0.1 A I_C = 1 A I_B = 0.2 A I_C = 2.5 A I_B = 0.5 A			1.1 1.2 1.3	V V V
h_{FE}*	DC Current Gain	I_C = 10 mA V_{CE} = 5 V I_C = 2 A V_{CE} = 5 V	10 8		 40	
V_f	Forward Voltage Drop	I_f = 2 A			2.5	V
 t_s t_f	RESISTIVE LOAD Storage Time Fall Time	V_{CC} = 250 V I_C = 2 A I_{B1} = 0.4 A I_{B2} = -0.4 A T_p = 30 μs (see fig. 2)	 2	 0.2	 2.9	 μs μs
 t_s t_f	INDUCTIVE LOAD Storage Time Fall Time	V_{CC} = 200 V I_C = 2 A I_{B1} = 0.4 A $V_{BE(off)}$ = -5 V R_{BB} = 0 Ω L = 200 μH (see fig. 1)		 0.6 0.1		 μs μs

∗ Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

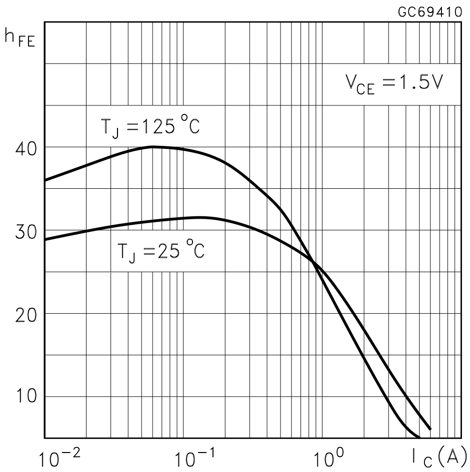
Safe Operating Areas



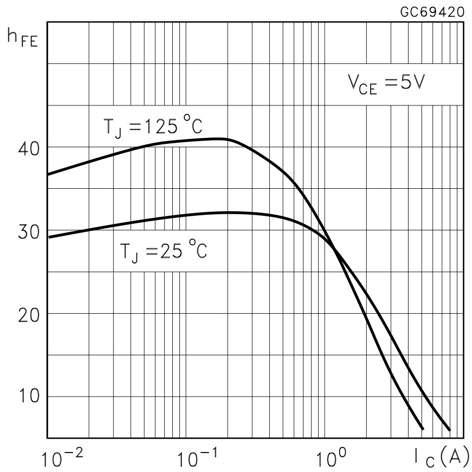
Derating Curve



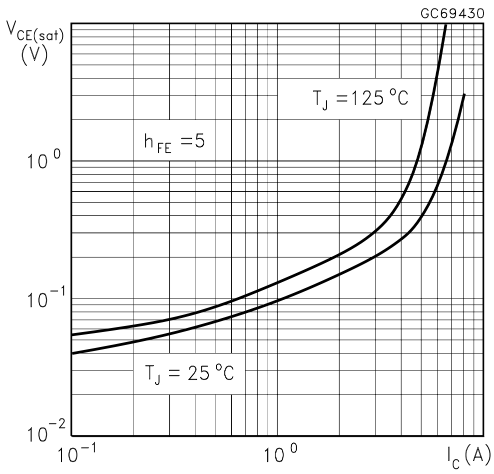
DC Current Gain



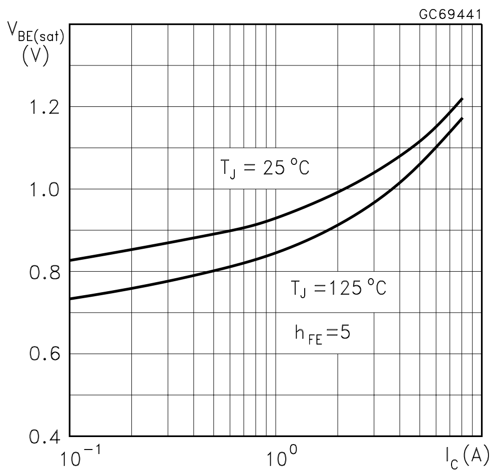
DC Current Gain



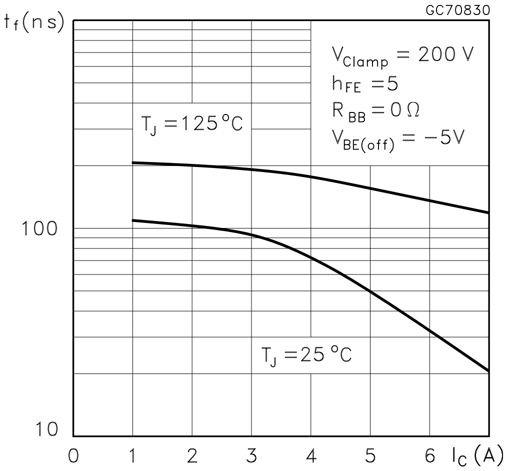
Collector Emitter Saturation Voltage



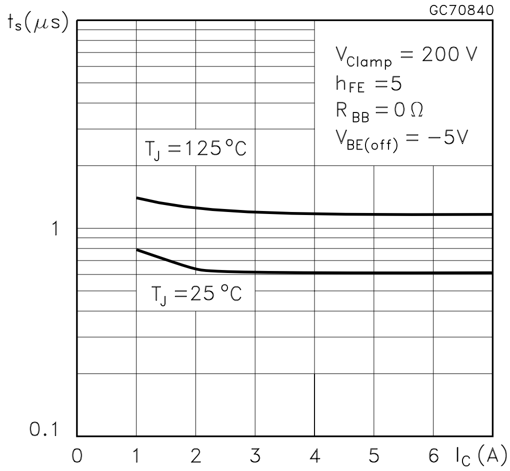
Base Emitter Saturation Voltage



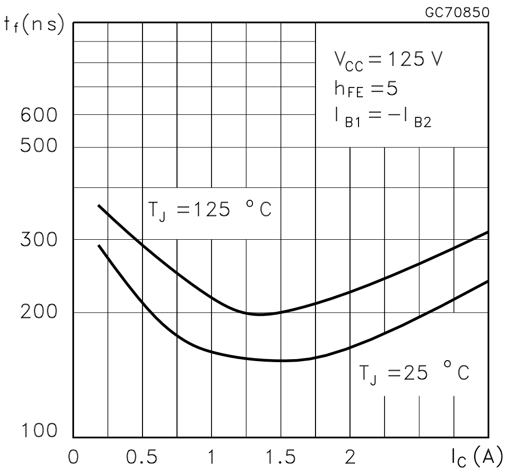
Inductive Fall Time



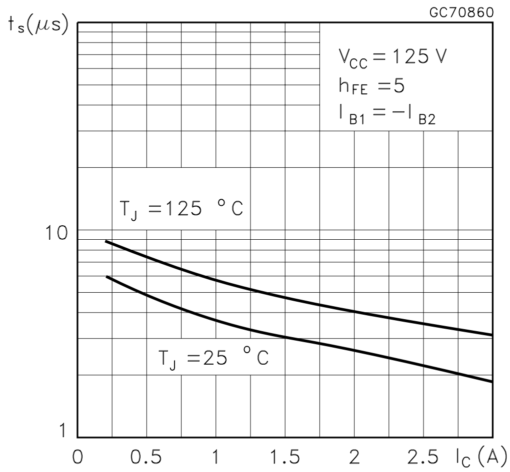
Inductive Storage Time



Resistive Load Fall Time



Resistive Load Storage Time



Reverse Biased SOA

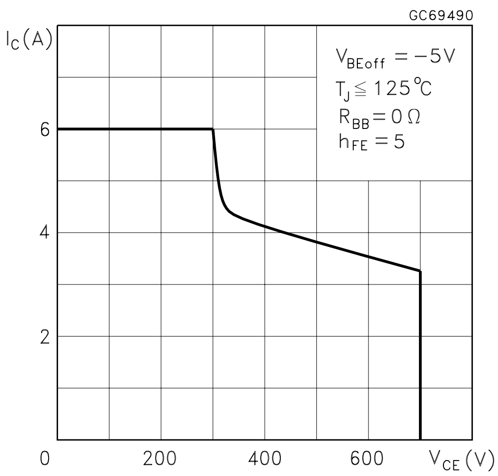


Figure 1: Inductive Load Switching Test Circuit.

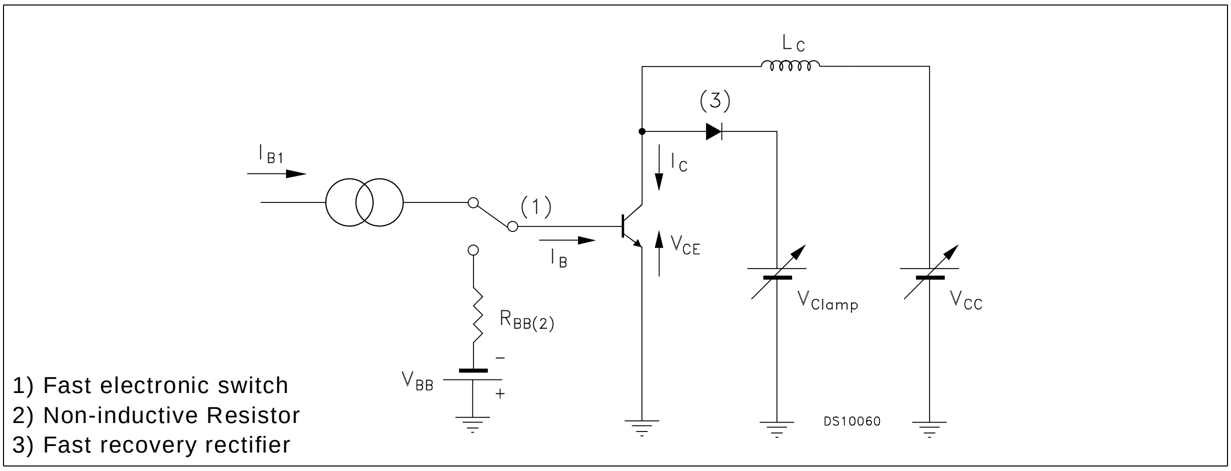
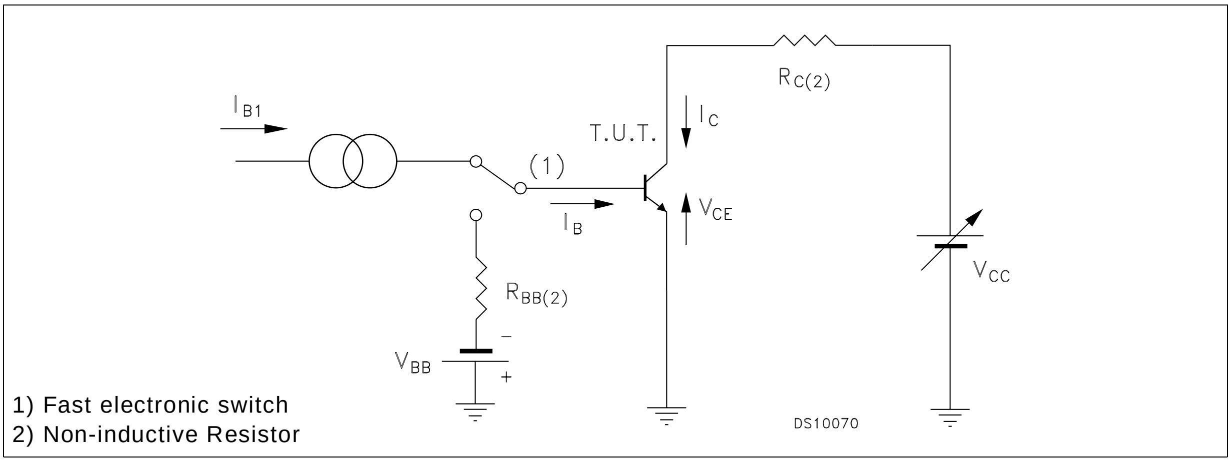
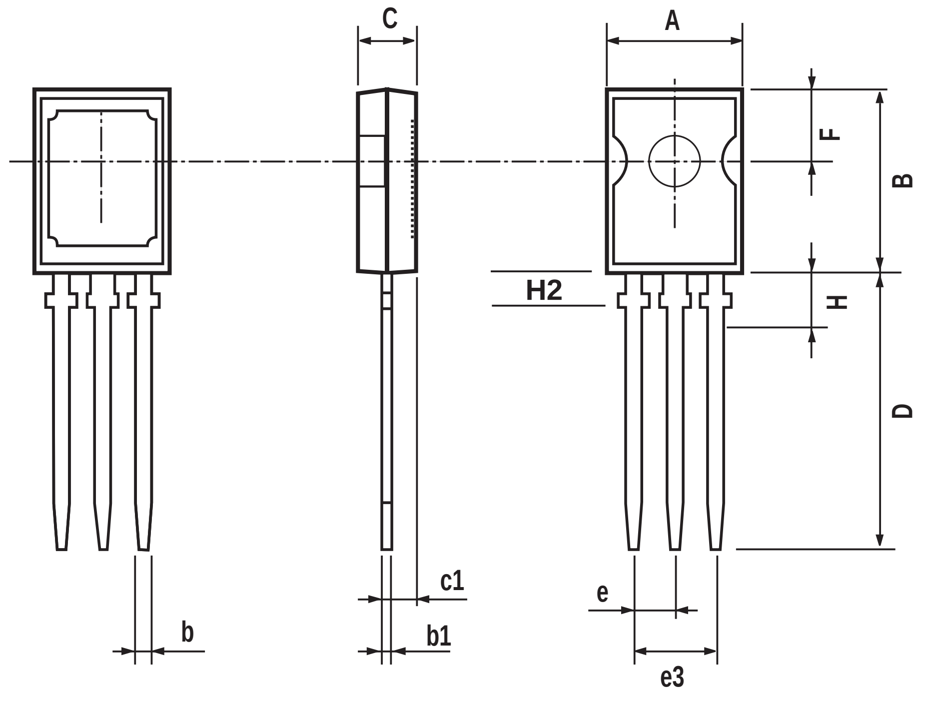


Figure 2: Resistive Load Switching Test Circuit.



SOT-82 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	7.4		7.8	0.291		0.307
B	10.5		10.8	0.413		0.444
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
C	2.4		2.7	0.04		0.106
c1	1.0		1.3	0.039		0.05
D	15.4		16	0.606		0.629
e		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
H			2.54		0.100	
H2		2.15			0.084	



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